Publication Details of Prof. (Dr.) Angsuman Sarkar as of 01-September-2021

(Click the links below to see the details)

Book Publication: 6

Contributed Book Chapter Publication: 10

Journal Publication: 86

Conference Publication: 52

List of Book Publication:

1. Angsuman Sarkar, Swapnadip De, Manash Chanda, Chandan KumarSarkar, “Low Power VLSI Design Fundamentals”, DE GRUYTER OLDENBOURG , Germany, August 2016, ISBN: 978-3-11-045529-8, Edition: 1st, No. of Pages:310, Price: 129,95 € / $182.00 / £97.99, Online Link

2. Angsuman Sarkar and Chandan Kumar Sarkar, “Solid State, Microelectronic and Optoelectronic Devices”, University Press (India) Pvt. Ltd., Hyderabad, India, Distributed by Orient BlackSwan Pvt. Ltd., January 1, 2012, ISBN: 978-81-7371-770-3,
Edition: 1st, No. of Pages:664, Price: 410 (INR), Online Link

3. Angsuman Sarkar, Swapnadip De and Chandan Kumar Sarkar, “VLSI design and EDA tools”, Scitech Publications (India) Pvt. Ltd. Chennai, India, January 1, 2014, ISBN:978-81-8371-497-6, Edition: 2nd, No. of Pages: 905, Price: 650 (INR), Online Link

4. Angsuman Sarkar; Swapnadip De; C K Sarkar, “VLSI Design and EDA Tools”, Scitech Publications (India) Pvt Ltd., Chennai, India, January 1, 2011, ISBN: 978-81-8371-452-5, Edition: 1st, No. of Pages:1430, Price: 750 (INR), Online Link

5. Angsuman Sarkar, “Subthreshold Modeling of Submicron MOSFETs Short Channel Mosfets: Conventional and Dual Material Gate (DMG)”, LAMBERT Academic Publishing, GmbH & Co. KG, Address: Dudweiler Landstraße 99, 66123 Saarbrücken, Germany, October 7, 2011, ISBN: 978-3-8465-2209-7, Edition: 1st, No. of Pages:104 Price: 49.00€, Online Link

6. Angsuman Sarkar, “Subthreshold Surface Potential Model for Short-Channel Mosfet: Using Pseudo 2d Analysis”, LAMBERT Academic Publishing, GmbH & Co. KG, Address: Dudweiler Landstraße 99, 66123 Saarbrücken, Germany, February 27, 2014, ISBN: 978-3659126093 Edition: 1st, No. of Pages: 84, Price: 35.50€ Online Link

List of Contributed Book Chapter Publication:

10. Title of the Book: “Emerging Trends in Terahertz Engineering and System Technologies Devices, Materials, Imaging, Data Acquisition and Processing”, Book Chapter Name: “Performance Estimation of Defected Ternary Photonic Crystal-Based Bandpass Filter Beyond 100 THz for All-Optical Circuit”, Authors: Arpan Deyasi, Angsuman Sarkar, Publisher: Springer, Singapore, Editor: A. Biswas et al., Date of Publication: March 2021, Print ISBN: 978-981-15-9765-7, Online ISBN: 978-981-15-9766-4, Online Link

9. Title of the Book: “Advanced Materials for Future Terahertz Devices, Circuits and Systems”, Book Chapter Name: “Analysis of Optical Performance of Dual-Order RAMAN Amplifier Beyond 100 THz Spectrum”, Authors: Rajarshi Dhar, Arpan Deyasi, Angsuman Sarkar, Publisher: Springer Singapore, , Editor: A. Acharyya et al., Date of Publication: March,2021, Print ISBN: 978-981-334-488-4, Electronic ISBN: 978-981-334-489-1, Online Link

8. Title of the Book: ”Computational Intelligence in Digital Pedagogy”, Book Chapter Name: “Authentic Pedagogy: A Project-Oriented Teaching–Learning Method Based on Critical Thinking”, Authors: Arpan Deyasi, Swapan Bhattacharyya, Pampa Debnath, Angsuman Sarkar, Publisher: Springer, Singapore, , Editor: A. Deyasi et al., Date of Publication: November 20, 2020, ISBN: 978-981-15-8743-6, Online Link

7. Title of the Book: ”Emerging Trends in Terahertz Solid-State Physics and Devices”, Book Chapter Name: “THz Bandpass Filter Design Using Metamaterial-Based Defected 1D Photonic Crystal Structure”, Authors: Arpan Deyasi, Angsuman Sarkar, Publisher: Springer, Singapore, Editor: A. Biswas et. al., Date of Publication: March 21, 2020, ISBN: 978-981-15-3234-4, Online LInk

6. Title of the Book: “Methodologies and Application Issues of Contemporary Computing Framework”, Book Chapter Name: “Investigation of the Effect of Barrier Layer Engineering on DC and RF Performance of Gate-Recessed AlGaN/GaN HEMT”, Authors: Shubham Mondal, Sritoma Paul, Angsuman Sarkar, Publisher: Springer Nature Singapore Pte Ltd. , Editor: J . K. Mandal et al., Date of Publication: 22 September 2018, 978-981-13-2344-7, Online Link

5. Title of the Book: “Nanotechnology Synthesis to Applications”, Book Chapter Name: “Nanoscience with Graphene”, Authors: Dr. Angsuman Sarkar, Publisher: CRC Press USA, Editor: S. Roy et. al., Date of Publication: January 1, 2018, ISBN: 9781138032736, Online Link

4. Title of the Book: “Nanotechnology Synthesis to Applications”, Book Chapter Name: “Electrical transport in Nanostructure”, Authors: Dr. Angsuman Sarkar, Publisher: CRC Press USA, Editor: S. Roy et. al. , Date of Publication: January 1, 2018, ISBN: 9781138032736, Online Link

3. Title of the Book: “Computational Science and Engineering: Proceedings of the International Conference on Computational Science and Engineering”, Book Chapter Name: “Analytical modeling and sensitivity analysis of dielectric-modulated junctionless gate all around gate stack—FET as biosensor”, Authors: A. Chakraborty, A. Sarkar, Publisher: CRC Press, USA, Editor: A. Deyasi et. al., Date of Publication: 19 December 2016, ISBN: 978-1-138-02983-5, Online Link

2. Title of the Book: “Intelligent computing,Communication and Devices Advances in Intelligent Systems and Computing”, Book Chapter Name:”An Analytical Surface Potential Model of Surrounding Gate Tunnel FET”, Authors: Soumen Paul, Angsuman Sarkar, Volume 308, 2015, pp 479-486, Publisher: Springer, Singapore, Editor: L. Jain et. al., Date of Publication: August 26, 2014, ISBN: 978-81-322-2011-, Online Link

1. Title of the Book: “TCAD Simulation for VLSI MOSFET”, Book Chapter Name: “Device Simulation Using SILVACO ATLAS Tool”, Authors: Dr. Angsuman Sarkar, Publisher: CRC Press, Taylor & Francis Group, UK, Editor: C.K.Sarkar, Date of Publication: May 16, 2013, ISBN: 978-1-46-651265-8, Online Link

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1. P. Debnath, A. Deaysi, U. Mondal, A. Sarkar, "Analytical investigation of double negative material based photonic filter performance at 1550 nm", JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, Vol. 23, No. 7-8, July – August 2021, p. 319 - 326
2. S Sinha, T Paul, S Mishra, S Shaw, K Biswas, D De, A Sarkar, In Vivo Biointeraction and Alleviation of Toxicity of MWCNTs upon Functionalization with ssDNA in a Caenorhabditis elegans Model, Journal of Electronic Materials, Springer, 1-17
3. P Mitra, J Bhaumik, A Sarkar, Decoupling Capacitor Estimation and Allocation using Optimization Techniques for Power Supply Noise Reduction in System-on-Chip, Journal of Electronic Testing, Springer, 1-5
4. S Misra, SM Biswal, B Baral, SK Swain, A Sarkar, SK Pati, Analytical modelling of a Cyl-JLAM MOSFET in the subthreshold region using distinct device geometry, Journal of Computational Electronics, Springer, 20 (1), 480-491
5. B Das, N Chand, A Sarkar, Review the Performance of Different Digital Modulation Techniques with Suitable Error Control Codes in Telehealth Services, Advances in Medical Physics and Healthcare Engineering, 341-352
6. N Chand, S Bhattacharyya, A Sarkar, A Novel Encryption Technique to Protect Patient Health Information Electronically Using Playfair Cipher 15 by 14 Matrix, Advances in Medical Physics and Healthcare Engineering, 423-431
7. A Chakraborty, A Sarkar, A Sarkar, Analytical model and sensitivity analysis of a gate-engineered dielectric modulated junctionless nanowire transistor-based biosensor, Electronic Devices, Circuits, and Systems for Biomedical Applications, 69-93
8. R Dhar, A Deyasi, A Sarkar, Analysis of Optical Performance of Dual-Order RAMAN Amplifier Beyond 100 THz Spectrum, Advanced Materials for Future Terahertz Devices, Circuits and Systems 727, 193
9. A Deyasi, A Sarkar, Performance Estimation of Defected Ternary Photonic Crystal-Based Bandpass Filter Beyond 100 THz for All-Optical Circuit, Emerging Trends in Terahertz Engineering and System Technologies: Devices
10. A Deyasi, N Pramanik, A Sarkar, Detecting Signature of Virus Using Metamaterial-Based One-Dimensional Multi-layer Photonic Crystal Structure Under Polarized Incidence, Modern Techniques in Biosensors, 199-214
11. A Deyasi, S Bhattacharyya, P Debnath, A Sarkar, Authentic Pedagogy: A Project-Oriented Teaching–Learning Method Based on Critical Thinking, Computational Intelligence in Digital Pedagogy, 1-20

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2. P Mitra, A Sarkar, "Soft Computing Techniques Based CAD Approach for Power Supply Noise Reduction in System-on-Chip", Journal of Electronic Testing, 1-5, 2020, Springer
3. S. Misra, S. M. Biswal, B. Baral, S. K. Swain, A. Sarkar & S. K. Pati, "Analytical modelling of a Cyl-JLAM MOSFET in the subthreshold region using distinct device geometry", Journal of Computational Electronics (2020), Published: 15 September 2020, Springer
4. A. Basak & A. Sarkar, ' Quantum Analytical Model for Lateral Dual Gate UTBB SOI MOSFET for Analog/RF Performance', Silicon (2020), Springer
5. S Sinha, S Shaw, K Biswas, D De, SC Das, A Sarkar, J Bandyopadhyay, 'Favorable influence of ssDNA-functionalized SWCNT on the navigation pattern of C. elegans', Microsystem Technologies, 1-14, June 2020, Springer
6. A. Deyasi, U. Dey, S. Das, S. De & A. Sarkar, "Computing Photonic Bandgap from Dispersion Relation for TM Mode Propagation Inside Metamaterial-based 1D PhC", Micro and Nanosystems (2020) 12: 1., Bentham Science

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2. S. Paul, S. Mondal, & A. Sarkar, "Characterization and analysis of low-noise GaN-HEMT based inverter circuits", Microsystem Technologies, Springer, Online First on 20-Aug-2019
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